

Abstract of the disclosure

Disclosed is a semiconductor device with a resistor pattern and methods of fabricating the same. Embodiments of the present invention provide a method of fabricating a resistor pattern having high sheet resistance by using a polycide layer for a gate electrode in a semiconductor device with the resistor pattern. Embodiments of the invention also provide a semiconductor device with a resistor pattern that is formed narrower than the minimum line width that can be defined in a photolithographic process so that sheet resistance thereof increases, and a method of fabricating the same.

10